

Silicon PNP Power Transistors

2SB1368

DESCRIPTION

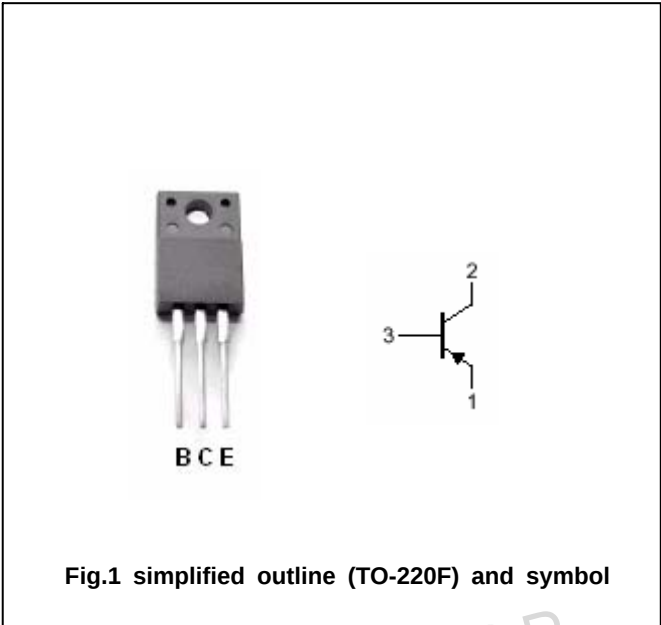
- With TO-220F package
- Complement to type 2SD2060
- Low collector saturation voltage:
 $V_{CE(SAT)}=-1.7V(Max)$ at $I_C=-3A, I_B=-0.3A$
- Collector power dissipation:
 $P_C=25W(T_C=25\text{ }^{\circ}C)$

APPLICATIONS

- With general purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings (Ta=25 °C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-4	A
I_B	Base current		-0.4	A
P_C	Collector dissipation	$T_a=25$	2.0	W
		$T_C=25$	25	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA ; I_B=0$	-80			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-3A ; I_B=-0.3A$		-1.0	-1.7	V
V_{BE}	Base-emitter on voltage	$I_C=-3A ; V_{CE}=-5V$		-1.0	-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-80V ; I_E=0$			-30	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V ; I_C=0$			-100	μA
h_{FE-1}	DC current gain	$I_C=-0.5A ; V_{CE}=-5V$	40		240	
h_{FE-2}	DC current gain	$I_C=-3A ; V_{CE}=-5V$	15			
f_T	Transition frequency	$I_C=-0.5A ; V_{CE}=-5V$		9.0		MHz
C_{OB}	Collector output capacitance	$f=1MHz ; V_{CB}=10V$		130		pF

◆ h_{FE-1} Classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

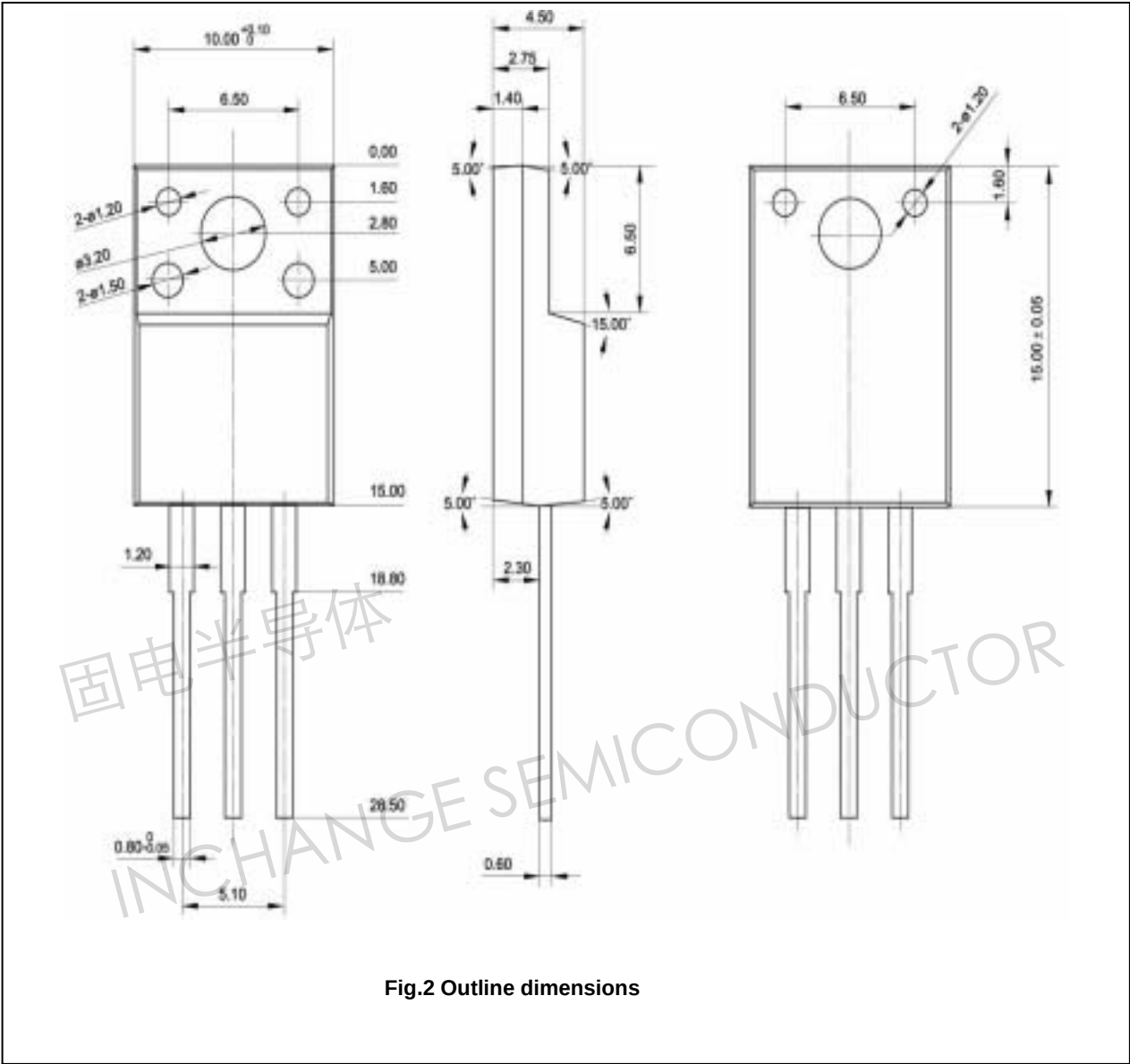


Fig.2 Outline dimensions

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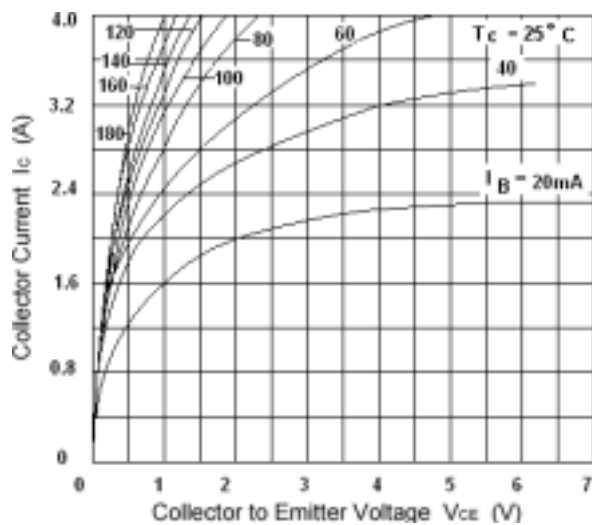


Fig.3 Static Characteristic

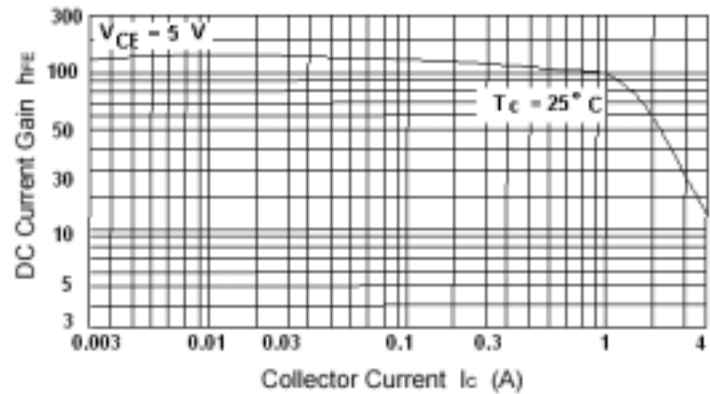


Fig.4 DC current Gain

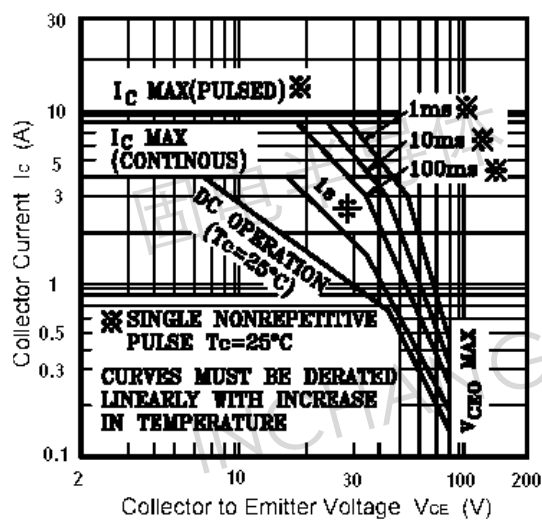


Fig.5 Safe Operating Area

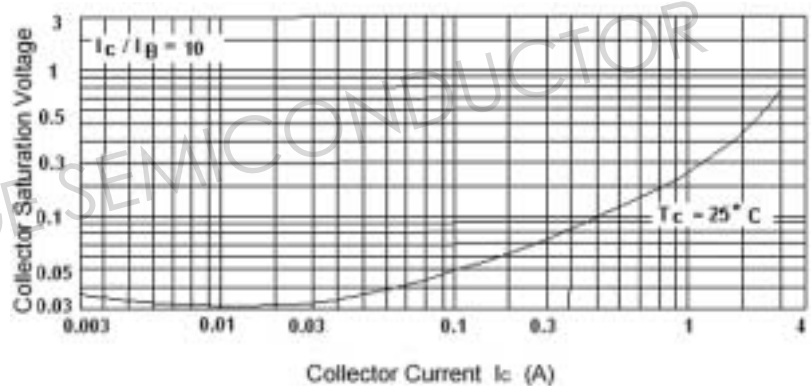


Fig.6 Collector-Emitter Saturation Voltage